A 2W 9.5-16.5 GHz GaN Power Amplifier With 30% PAE Using Transformer-Based Output Matching Network

Xiao Sun[1], Xu Zhu[2], Yong Wang[1], Pei-Ling Chi[3], Tao Yang[1]

[1]University of Electronic Science and Technology of China, China

[2]Northern Institute of Electronic Equipment of China, China

[3]National Chiao Tung University, Taiwan , China

Outline

- Introduction

- Design approach

- Measured performances

- Conclusion

Introduction

- ## Power Amplifier (PA)

  — Important part in communication systems
  — Output power, efficiency, bandwidth, linearity
  — Critical trade-off: bandwidth vs efficiency

- ## Large Demands for PAs

  — Broadband or multiband operation
  — High efficiency

DC Power P_{DC}

RF Input Power

PA

RF Output Power
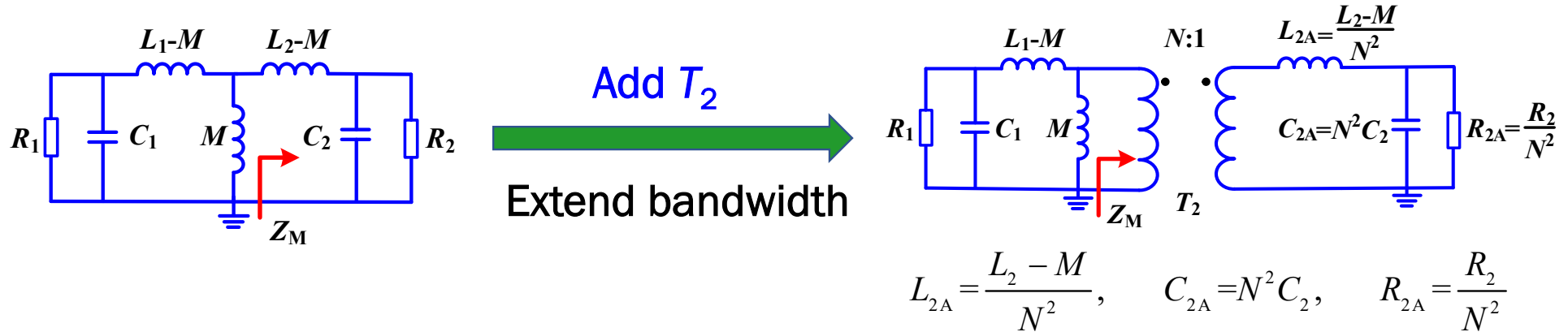
P_{In}

P_{OUT}
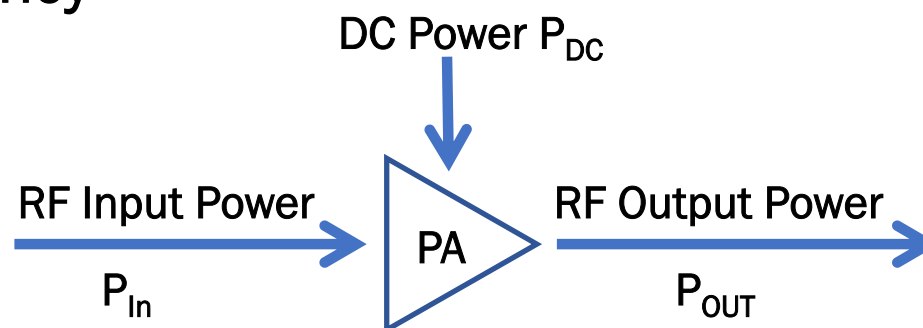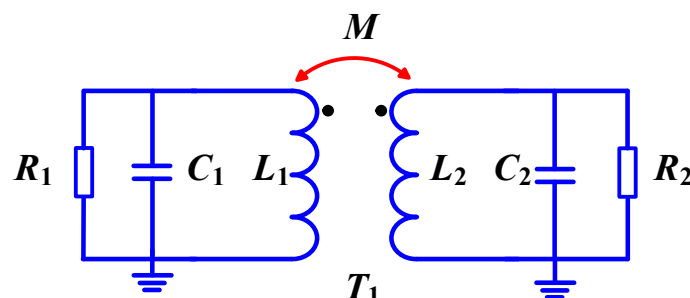
Design approach

- Transformer structure can cover multioctave bandwidth
- Large coupling coefficient
- Require multiple metal layers
- Only two metal layers in GaN technology

Design approach

Add T_2

Extend bandwidth

$$BW = \frac{\omega_0}{2\pi}\left(\sqrt{\frac{1}{1-k}} - \sqrt{\frac{1}{1+k}}\right), \quad k \le min\left(\sqrt{\frac{1}{N_1}}, \sqrt{N_1}\right)$$

BW is limited by impedance ratio N_1

$$L_{2A} = \frac{L_2 - M}{N^2}, \qquad C_{2A} = N^2 C_2, \qquad R_{2A} = \frac{R_2}{N^2}$$

$$N_1 = \frac{R_2}{R_1} < \frac{R_{2A}}{R_1}, \qquad N_2 = \frac{1}{N^2} = \frac{R_{2A}}{R_2} < \frac{R_{2A}}{R_1}$$
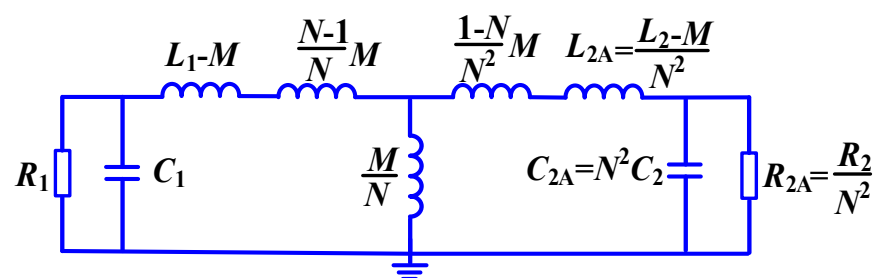
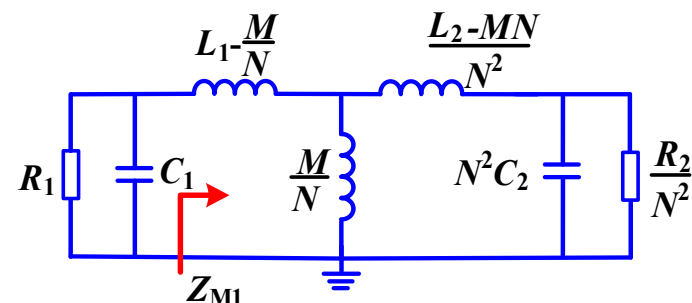$R_1 \longrightarrow R_2 \longrightarrow R_{2A} = 50\ \Omega$
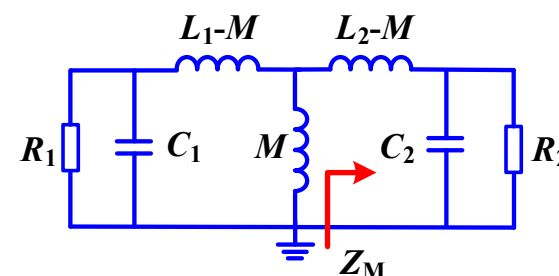
Impedance ratio decrease
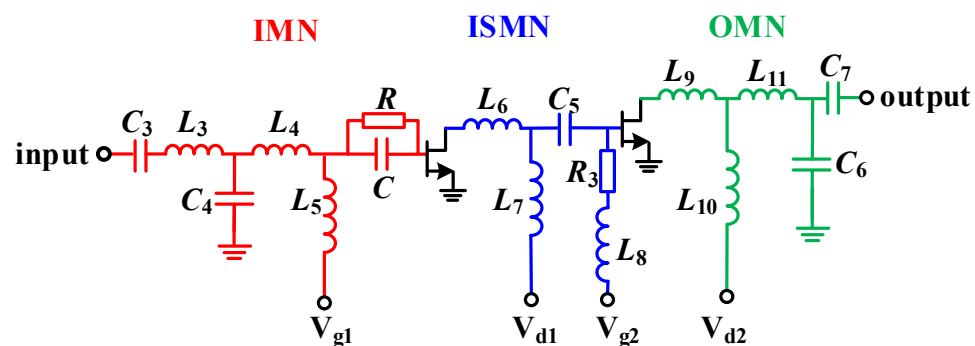The bandwidth increase

Norton transformation

Final network

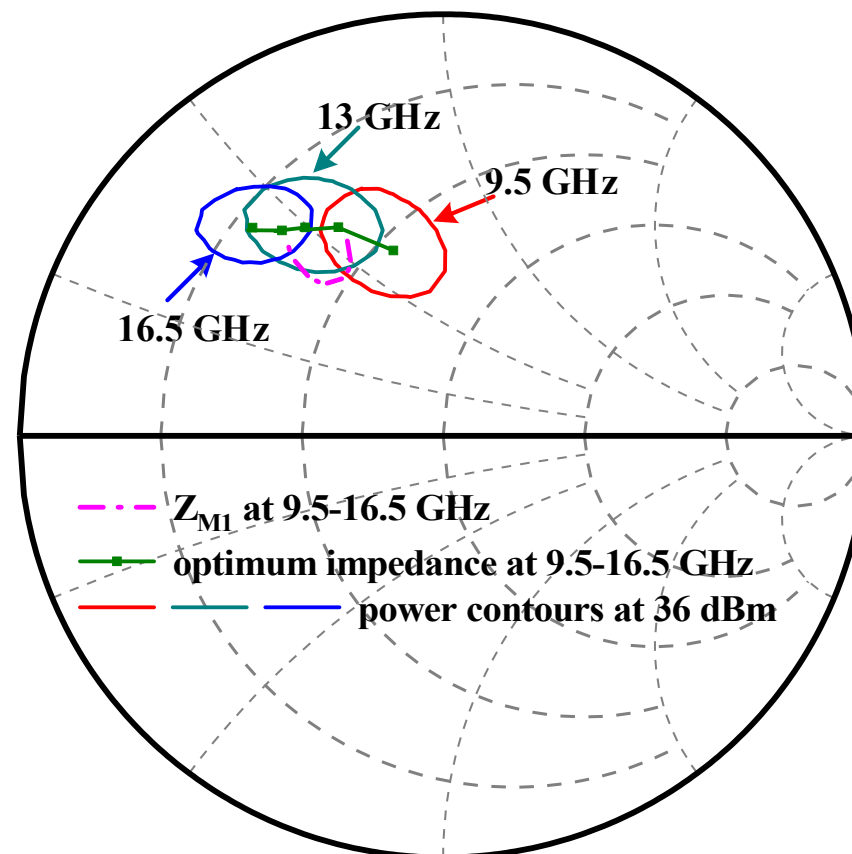- Exhibit the same circuit form
- A much wider matching bandwidth

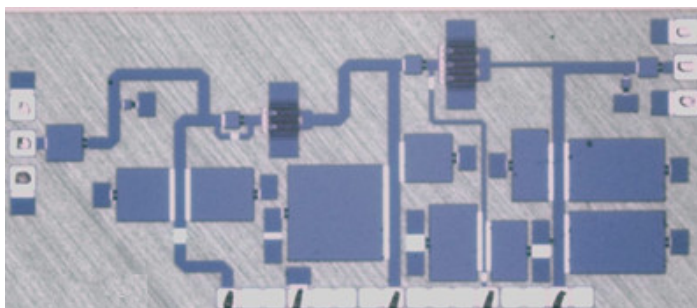# Design approach

Matching performance

Good performance has been
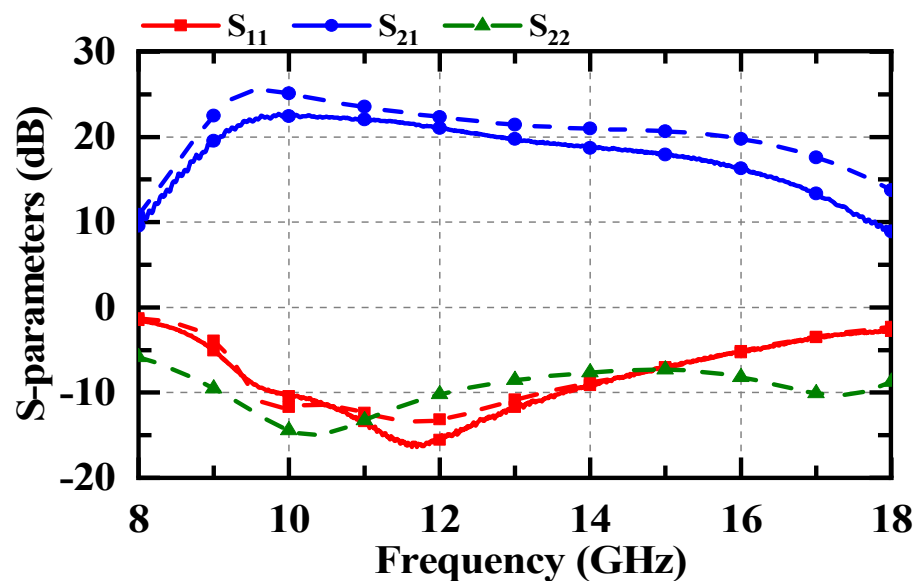achieved with the proposed circuit

Design approach

- Final MMIC

  Size: 2.9 mm × 1.2 mm

- Configuration:

  — Transformer-based output matching network
  — 2 stages amplification
  — Transistor size:
    — Power stage: 6×125 µm
    — Driver stage: 4×125 µm
  — Frequency band: 9.5-16.5 GHz
  — Bare die/50 Ω fully matched
  — Drain biasing: 23V

Measured performances

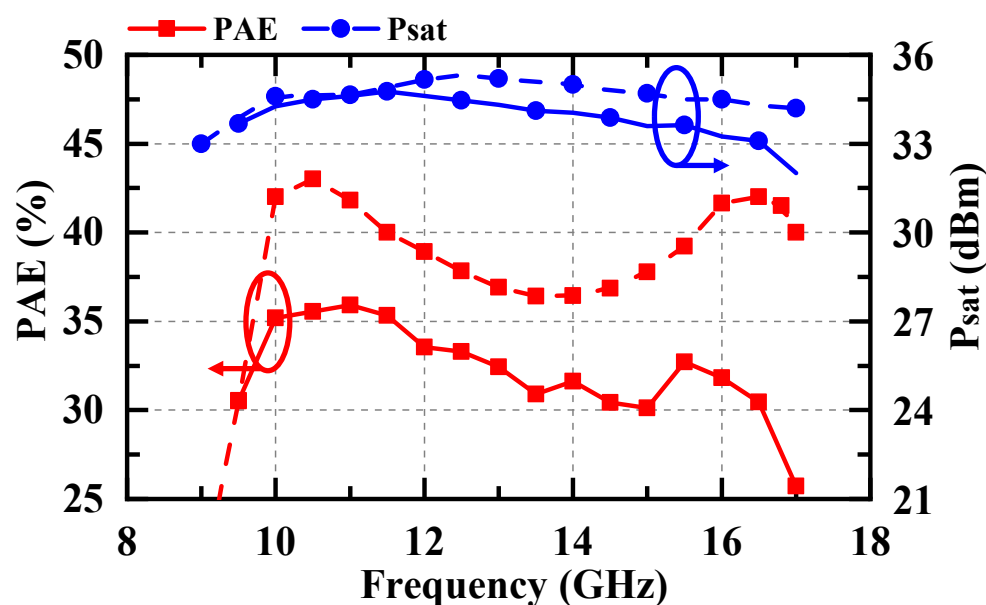- ## Small signal

- Measured : Solid Traces
- Modeled: Dash Traces
- Small gain is around 20 dB
- Input return loss < 6 dB
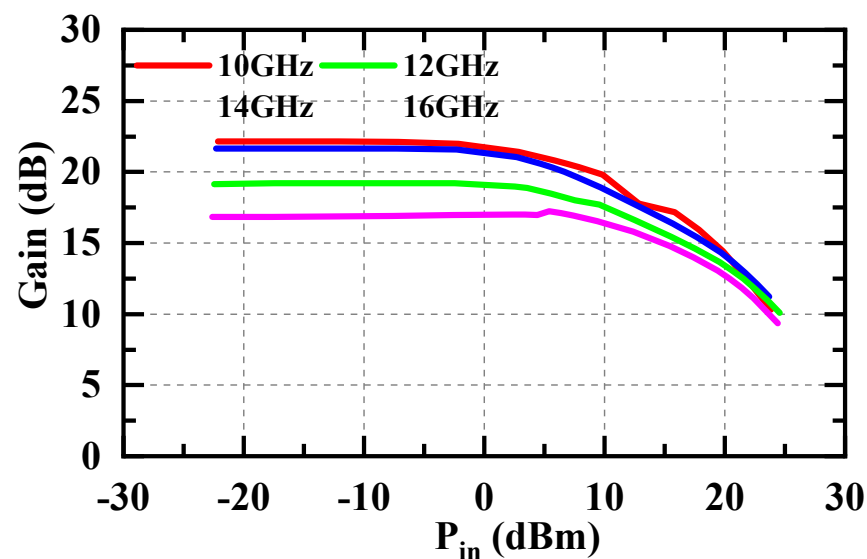- Output return loss < 10 dB

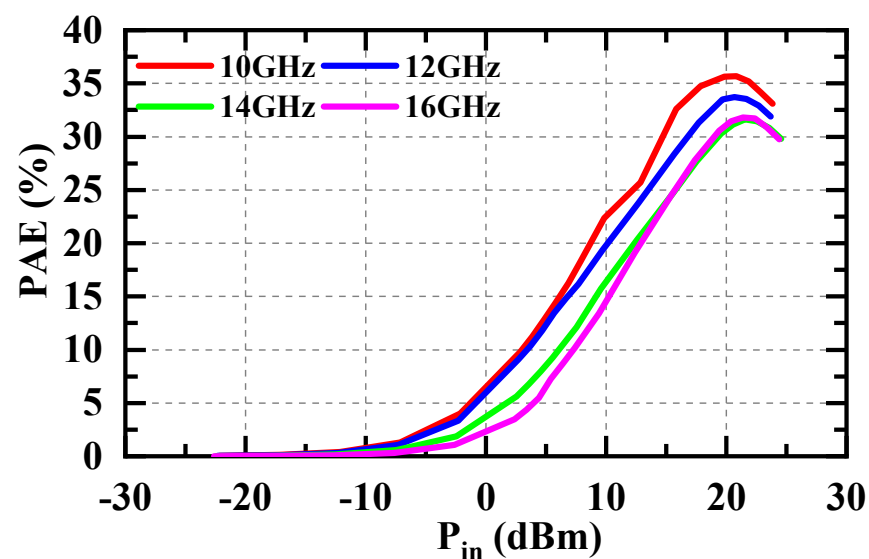# Measured performances

- ## Large signal vs Frequency

- Measured : Solid Traces
- Modeled: Dash Traces
- Peak power of 34.8 dBm and 35.4% PAE at 11.5 GHz
- Greater than 30% PAE maintained over full 9.5-16.5 GHz bandwidth

- Large signal vs Pin

Gain vs Pin

PAE vs Pin

Comparison

Ref.	Tech	Freq. (GHz)	Gain (dB)	P_{sat} (dBm)	PAE (%)	Area (mm^2)
[12]	0.25 µm GaN	9-10 13.5-16	10-12	36.5-37.2 35-36.4	31-36.5 30-35.7	3.78
[13]	0.25 µm GaN	6-10.5 10.5-18	17-27 15-22	34-36 34-38.5	15-34	5.4
[14]	0.25 µm GaN	7-17	13.1-18.6	35.7-37.5	10.2-12.3	11.15
[15]	0.25 µm GaN	10.5-15.5	15-21.2	37-39.8	35-42.2	6.5
This work	0.25 µm GaN	9.5-16.5	15-22.4	33.1-34.7	30.1-35.9	3.48

- The proposed PA achieves a wider bandwidth with high PAE and small size

Conclusion

- A transformer-based output matching network

- Broadband power amplifier

- High efficiency and small size

- Apply in the electronic warfare systems and radar systems

Thank You !